

General Description

The HSH0115 uses advanced trench MOSFET technology to provide excellent $R_{DS(ON)}$ and gate charge for use in a wide variety of other applications.

The HSH0115 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

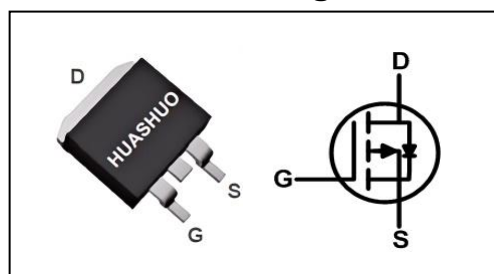
Features

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench Technology

Product Summary

V_{DS}	-100	V
$R_{DS(ON),typ}$	90	m Ω
I_D	-30	A

TO-263 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-30	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-20	A
I_{DM}	Pulsed Drain Current ²	-90	A
EAS	Single Pulse Avalanche Energy ³	310	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	98	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.2	$^\circ C/W$

P-Ch 100V Fast Switching MOSFETs
Electrical Characteristics ($T_J=25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-10A$	---	90	108	$m\Omega$
		$V_{GS}=-4.5V$, $I_D=-8A$	---	96	120	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.2	-1.8	-2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-100V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	-1	μA
		$V_{DS}=-100V$, $V_{GS}=0V$, $T_J=125^{\circ}\text{C}$	---	---	-100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V$, $I_D=-10A$	---	26	---	S
Q_g	Total Gate Charge	$V_{DS}=-50V$, $V_{GS}=-10V$, $I_D=-10A$	---	72	---	nC
Q_{gs}	Gate-Source Charge		---	8.4	---	
Q_{gd}	Gate-Drain Charge		---	17.3	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-50V$, $V_{GS}=-10V$, $R_G=9\Omega$, $R_L=5\Omega$	---	12	---	ns
T_r	Rise Time		---	18	---	
$T_{d(off)}$	Turn-Off Delay Time		---	115	---	
T_f	Fall Time		---	42	---	
C_{iss}	Input Capacitance	$V_{DS}=-50V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	3769	---	pF
C_{oss}	Output Capacitance		---	72	---	
C_{rss}	Reverse Transfer Capacitance		---	66	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-30	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^{\circ}\text{C}$	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F=-14A$, $di/dt=-100A/\mu s$, $T_J=25^{\circ}\text{C}$	---	45	---	nS
Q_{rr}	Reverse Recovery Charge		---	99	---	nC

Note :

1.Repetitive Rating: Pulse width limited by maximum junction temperature.

2.EAS condition: $T_J=25^{\circ}\text{C}$, $V_{DD}=-50V$, $V_G=10V$, $R_G=25\Omega$, $L=0.5\text{mH}$.

3.Repetitive Rating: Pulse width limited by maximum junction temperature.



Typical Characteristics

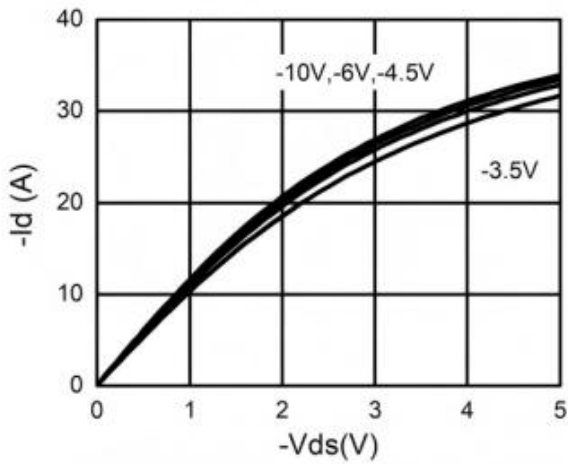


Figure 1. Output Characteristics

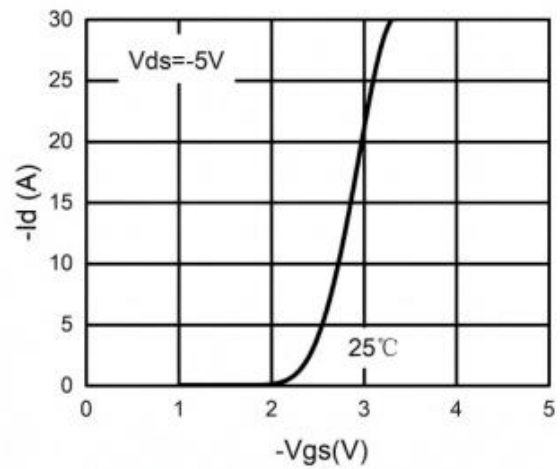


Figure 2. Transfer Characteristics

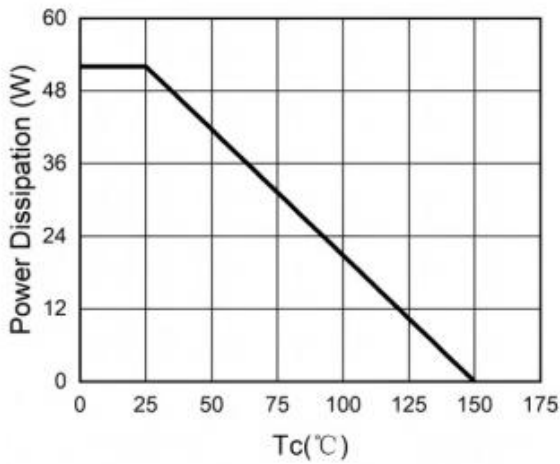


Figure 3. Power Dissipation

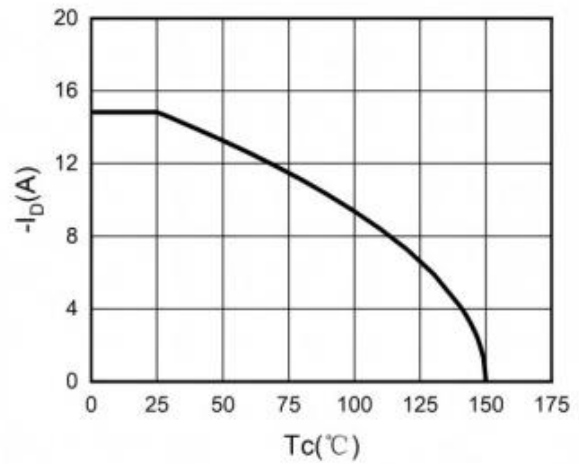


Figure 4. Drain Current

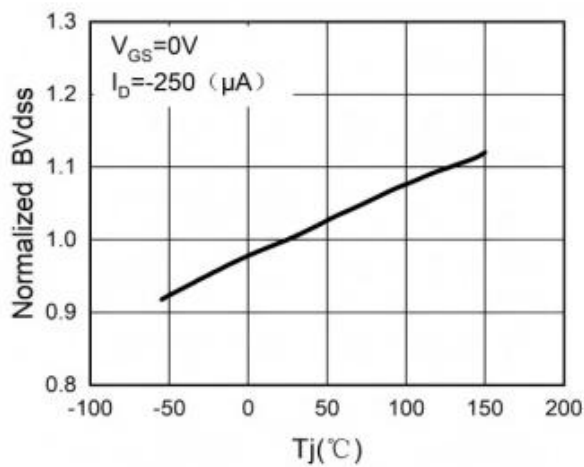


Figure 5. BV_{DSS} vs Junction Temperature

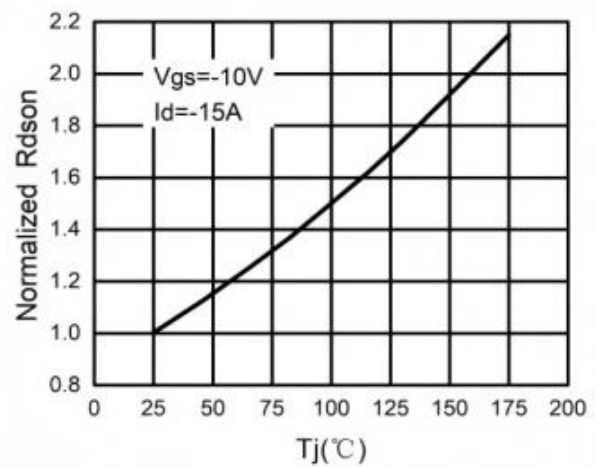


Figure 6. $R_{DS(ON)}$ vs Junction Temperature



P-Ch 100V Fast Switching MOSFETs

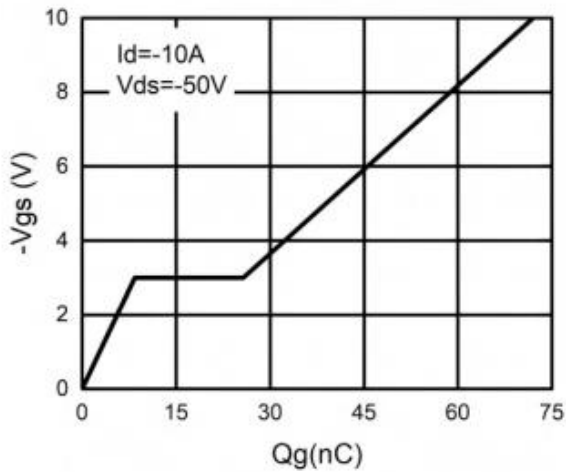


Figure 7. Gate Charge Waveforms

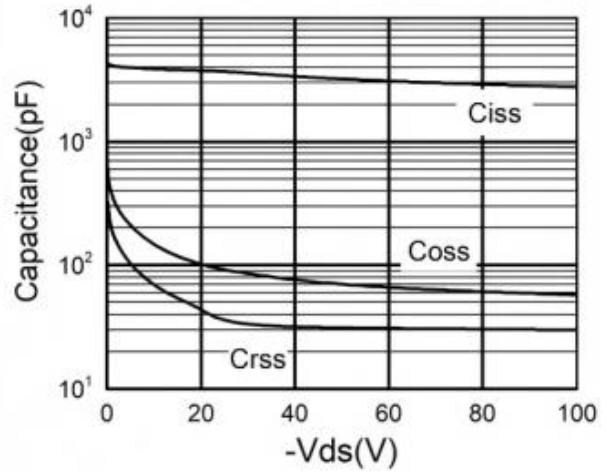


Figure 8. Capacitance

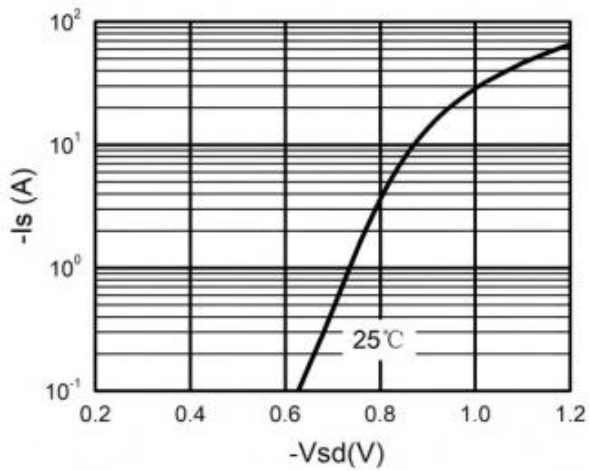


Figure 9. Body-Diode Characteristics

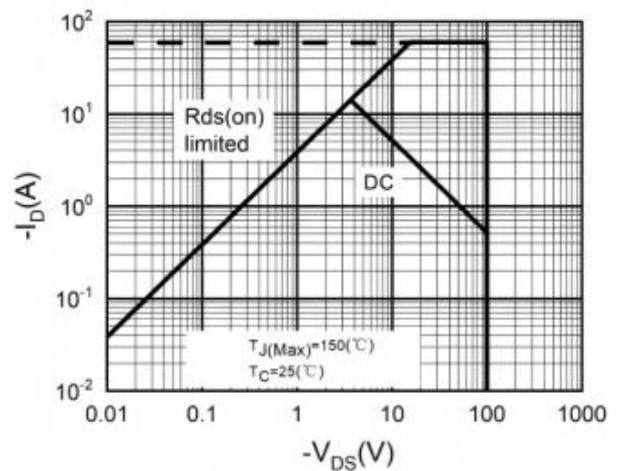
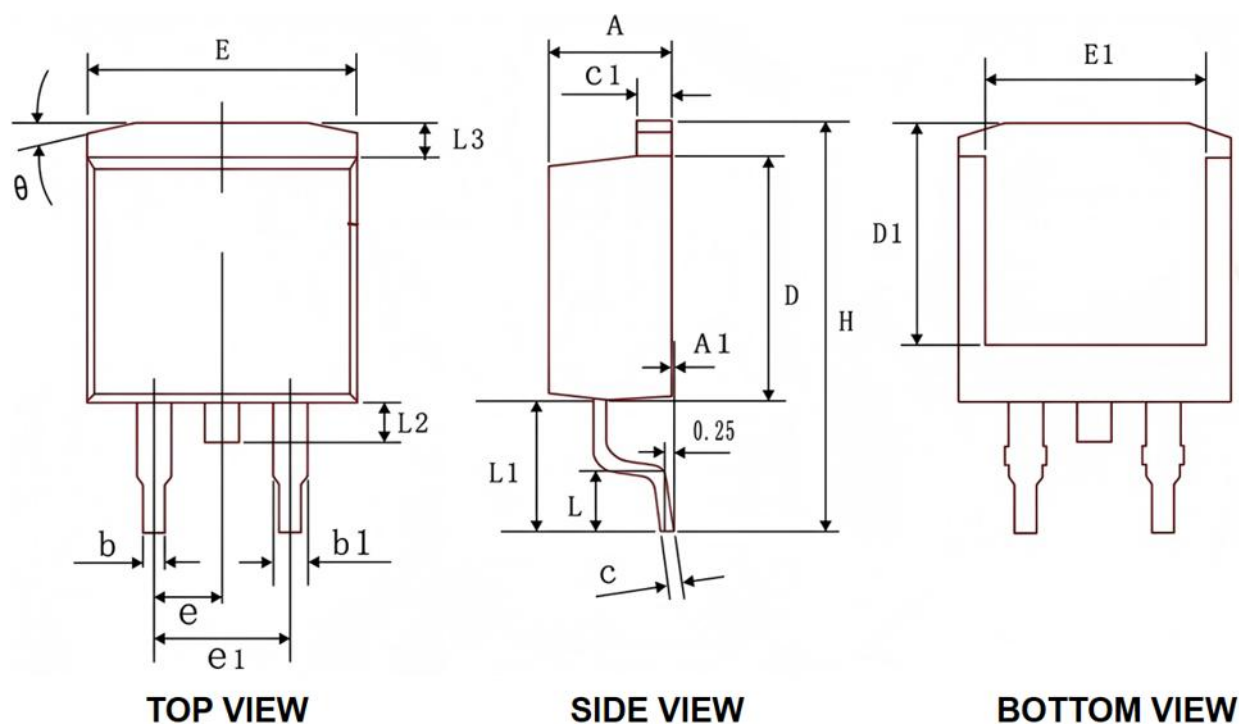


Figure 10. Maximum Safe Operating Area

Ordering Information

Part Number	Package code	Packaging
HSH0115	TO-263	800/Tape&Reel

TO-263 Package Outline



COMMON DIMENSIONS(UNIT OF MEASURE - MM)

SYMBOL	MIN	NOM	MAX
A	4.37	4.57	4.77
A1	0.00	-	0.25
b	0.70	0.83	0.96
b1	1.00	1.24	1.47
C	0.35	0.45	0.55
C1	1.25	1.30	1.35
D	8.50	8.90	9.30
D1	7.50	8.00	8.50
H	14.7	15.20	15.7
E	9.80	10.08	10.4
E1	7.35	7.80	8.25
e1	4.93	5.08	5.23
L	2.00	2.30	2.60
L1	4.50	4.75	5.00
L2	1.30	1.53	1.75
L3	1.10	1.29	1.47
e	2.54 BSC		
θ	13°TYP		

HSH0115 Marking:

